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The invention relates to the field of obtaining films of metal oxides, particularly of In_2O_3, with great dimensions of the flat atomic surface of crystallites.

The method for obtaining thin films of oxide semiconductors includes deposition of films by spray pyrolysis at the temperature of 450...550°C from aqueous $InCl_3$ solutions with the metal salt concentration in the solution exceeding 0.2M with subsequent annealing in the neutral or oxygen-containing atmosphere at a temperature exceeding 1000°C.

Claims: 2
Fig.: 3